

ABSTRACT

According to one embodiment, a memory device includes:
a first conductive layer; a first conductive film extending
in a first direction above the first conductive layer; a
5 first semiconductor film extending in the first direction
between the first conductive layer and the first conductive
film and intersecting the first conductive layer; a second
semiconductor film that is in contact with the first
semiconductor film, extends in the first direction between
10 the first conductive layer and the first conductive film,
and faces the first conductive film; a first insulating
film provided between the first conductive layer and the
first semiconductor film; and a second insulating film
provided between the first conductive film and each of the
15 first semiconductor film and the second semiconductor film.